

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

ATTORNEY DOCKET NO. 5342B

Eugene A. Fitzgerald
APPLICANT

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EXAMINER

1066 U.S. PTO
09/761497



U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA	5,208,182	5/4/93	Narayan et al.	438	509	11/12/91
TTN	AB	5,252,173	10/12/93	Inoue	438	509	11/22/91
TTN	AC	5,279,687	01/18/94	Tuppen et al.	148	33.2	02/27/90
TTN	AD	6,117,750	09/12/00	Bensahel et al.	438	478	12/21/98
TTN	AE	5,210,052	05/11/93	Takasaki	438	509	05/13/92
TTN	AF	5,221,413	06/22/93	Brasen et al.	117	89	04/24/91
TTN	AG	5,308,444	05/03/94	Fitzgerald, Jr. et al.	117	90	05/28/93
TTN	AH	5,442,205	08/15/95	Brasen et al.	257	191	09/09/93
TTN	AI	5,810,924	09/22/98	Legoues et al.	117	89	06/07/95
TTN	AJ	6,107,653	08/22/00	Fitzgerald	257	191	06/23/98

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TTN	AK	63073398	3/29/88	Japan	←	—	yes (abstract)
	AL						
	AM						
	AN						
	AO						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP	"Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si"; by Fitzgerald et al. 1992 American Vacuum society; pages 1807-1819
TTN	AQ	"GeSi/Si NANOSTRUCTURES" by E.A. Fitzgerald; Department of Materials Science, Massachusetts Institute of Technology (1995) pgs; 1-15

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DATE CONSIDERED 01/31/2002

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TN	AA	4,900,372	02/13/1990	Lee et al.	148	33.4	03/02/1989
	AB						
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	AI						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AP	Hsin-Chiao Luan et al., "High-quality Ge epilayers on Si with low threading-dislocation densities," <i>Applied Physics Letters</i> , American Institute of Physics, New York, Vol, 75, No. 19, November 8, 1999, pages 2909-2911.
	AQ	

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	DOCUMENT NUMBER	DESCRIPTION
TTN	AP	G. Kissinger et al., "Stepwise Equilibrated Graded Ge _x Si _{1-x} Buffer With Very Low Threading Dislocation Density on Si(001)," <i>Applied Physics Letters</i> 66 (16), April 17, 1995, of the 1995 American Institute of Physics Literature, pages 2083-2085.
	AQ	

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